Product data sheet

1. General description

Ultrafast, epitaxial rectifier diode in a SOD113 (TO-220F) plastic package.

2. Features and benefits

- Fast switching
- Low thermal resistance
- Soft recovery characteristic
- Isolated package
- Low forward voltage drop
- · High thermal cycling performance

3. Applications

- Output rectifiers in high frequency switched-mode power supplies
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Va	lues		Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			600			V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; $T_h \le 85$ °C; Fig. 1; Fig. 2; Fig. 3		9			А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; $T_h \le$ 85 °C; square-wave pulse		18		А	
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4				А	
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse			Α		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.12	1.26	V
		I _F = 8 A; T _j = 125 °C		-	1.03	-	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 6</u>		-	0.97	1.11	V
Dynamic	characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	32	60	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A 001aaa020
2	Α	anode		001aaa020
mb	mb	mounting base; isolated	1 2 SOD113 (2-lead TO-220F)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BYV29X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'	SOD113			

7. Marking

Table 4. Marking codes

Type number	Marking codes
BYV29X-600	BYV29X-600

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
I _{F(AV)}	average forward current	δ = 0.5; square-wave pulse; $T_h \le 85$ °C; Fig. 1; Fig. 2; Fig. 3	9	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; $T_h \le$ 85 °C; square-wave pulse	18	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	91	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	100	Α
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C

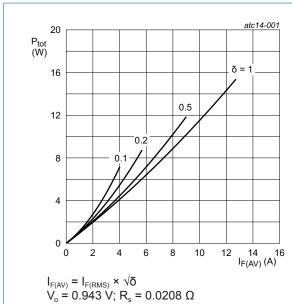
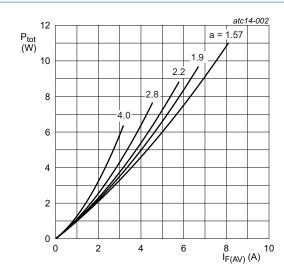


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ Vo = 0.943 V; Rs = 0.0208 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

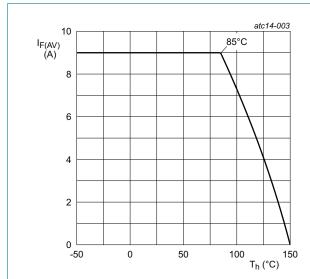


Fig. 3. Forward current as a function of heatsink temperature; maximum values

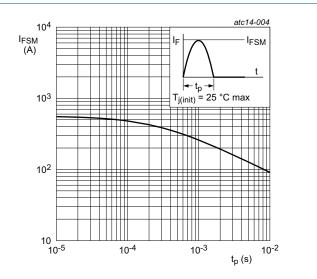
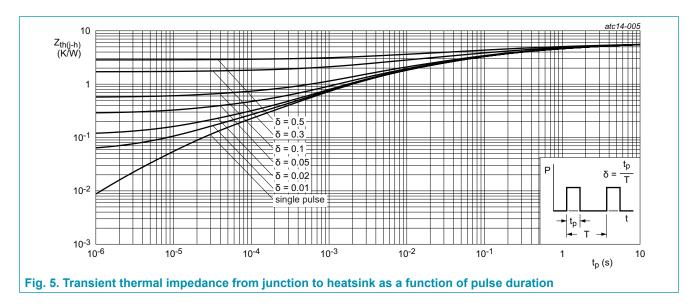


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)} thermal resista from junction t heatsink	thermal resistance	with heatsink compound; Fig. 5	-	-	5.5	K/W
	_	without heatsink compound	-	-	5.9	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W



10. Isolation characteristics

Table 6. Isolation characteristics

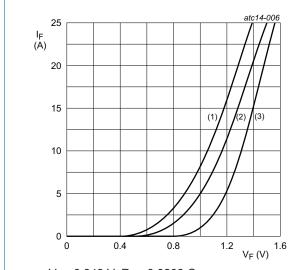
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink	-	10	-	PF

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11. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					•
V _F	forward current	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.12	1.26	V
		I _F = 8 A; T _j = 125 °C	-	1.03	-	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 6</u>	-	0.97	1.11	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	2	50	μA
		V _R = 600 V; T _j = 100 °C	-	0.3	-	mA
		V _R = 600 V; T _j = 125 °C	-	-	3	mA
Dynamic	characteristics					
Q _r	reverse charge		-	37	-	nC
t _{rr}	reverse recovery time		-	32	60	ns
I _{RM}	peak reverse recovery current	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	2.3	-	А
dI _{rr} /dt	peak rate of fall of reverse recovery current		-	297	-	A/µs
Q _r	reverse charge		-	220	-	nC
t _{rr}	reverse recovery time		-	43	-	ns
I _{RM}	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	10	-	А
dI _{rr} /dt	peak rate of fall of reverse recovery current		-	655	-	A/µs
Q_r	reverse charge		-	165	-	nC
t _{rr}	reverse recovery time		-	59	-	ns
I _{RM}	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	5.6	-	А
dl _{rr} /dt	peak rate of fall of reverse recovery current		-	215	-	A/µs
Q _r	reverse charge		-	425	-	nC
t _{rr}	reverse recovery time		-	57	-	ns
I _{RM}	peak reverse recovery current	I _F = 8 A; V _R = 400 V; dI _F /dt = 500 A/μs; T _j = 125 °C; <u>Fig. 7</u>	-	15	-	А
dl _{rr} /dt	peak rate of fall of reverse recovery current		-	1661	-	A/µs
Q _r	reverse charge		-	315	-	nC
t _{rr}	reverse recovery time		-	70	-	ns
I _{RM}	peak reverse recovery current	I _F = 8 A; V _R = 400 V; dI _F /dt = 200 A/μs; T _j = 125 °C; <u>Fig. 7</u>	-	9	-	A
dI _{rr} /dt	peak rate of fall of reverse recovery current		-	1181	-	A/µs



 V_o = 0.943 V; R_s = 0.0208 Ω

(1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values

(3) $T_i = 25$ °C; maximum values Fig. 6. Forward current as a function of forward voltage

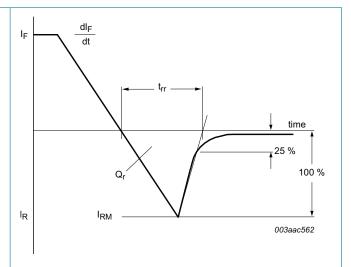
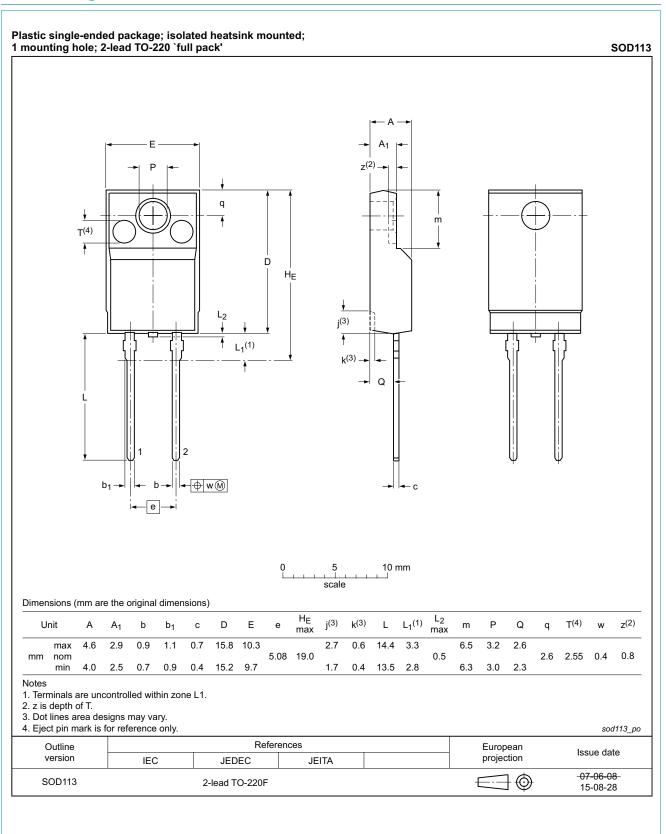


Fig. 7. Reverse recovery definitions; ramp recovery

12. Package outline



13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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14. Contents

1.	General description	. 1
2.	Features and benefits	. 1
3.	Applications	. 1
4.	Quick reference data	. 1
5.	Pinning information	. 2
6.	Ordering information	. 2
7.	Marking	. 2
8.	Limiting values	. 3
9.	Thermal characteristics	. 5
10	Isolation characteristics	. 5
11.	Characteristics	. 6
12	Package outline	. 8
	Legal information	
	Contents	

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